



# BTA316B-600BT

3Q Hi-Com Triac

6 August 2014

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series BT" triac will commute the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ °C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- High junction operating temperature capability
- High voltage capability
- Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only

## 3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

## 4. Quick reference data

Table 1. Quick reference data

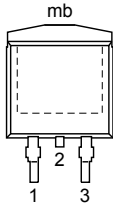

| Symbol       | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|--------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$    | repetitive peak off-state voltage    |   | -   | -   | 600 | V    |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ;<br>$t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>  | -   | -   | 140 | A    |
| $T_j$        | junction temperature                 |   | -   | -   | 150 | °C   |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{mb} \leq 120\text{ °C}$ ; <a href="#">Fig. 1</a> ;<br><a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 16  | A    |



| Symbol                         | Parameter                             | Conditions   | Min  | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|------|-----|-----|------|
| <b>Static characteristics</b>  |                                       |  |      |     |     |      |
| I <sub>GT</sub>                | gate trigger current                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | 2    | -   | 50  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | 2    | -   | 50  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | 2    | -   | 50  | mA   |
| <b>Dynamic characteristics</b> |                                       |  |      |     |     |      |
| dV <sub>D</sub> /dt            | rate of rise of off-state voltage     | V <sub>DM</sub> = 402 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit                  | 1000 | -   | -   | V/μs |
| di <sub>com</sub> /dt          | rate of change of commutating current | V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 16 A; dV <sub>com</sub> /dt = 20 V/μs; (snubberless condition); gate open circuit | 20   | -   | -   | A/ms |

## 5. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description                    | Simplified outline   | Graphic symbol  |
|-----|--------|--------------------------------|--|---|
| 1   | T1     | main terminal 1                |  <p><b>D2PAK (SOT404)</b></p> |  |
| 2   | T2     | main terminal 2                |  |   |
| 3   | G      | gate                           |  |   |
| mb  | T2     | mounting base; main terminal 2 |  |   |

## 6. Ordering information

**Table 3. Ordering information**

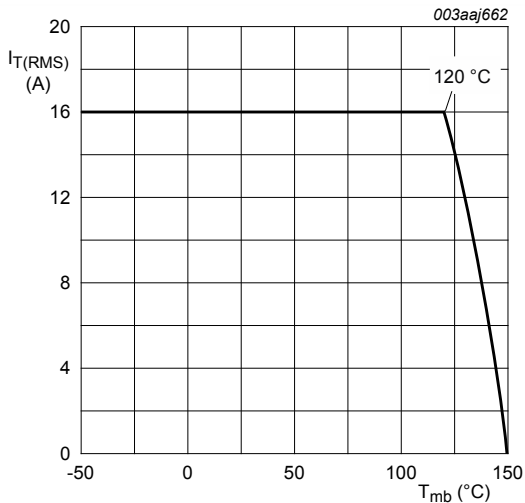
| Type number   | Package |  |         |
|---------------|---------|--|---------|
|               | Name    | Description  | Version |
| BTA316B-600BT | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

## 7. Limiting values

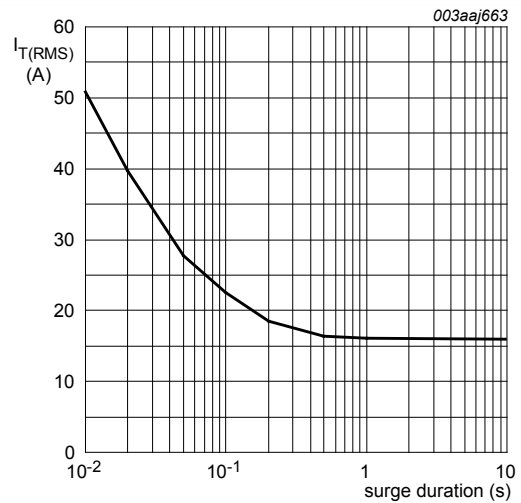
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions   | Min | Max | Unit                   |
|--------------|--------------------------------------|--|-----|-----|------------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |  | -   | 600 | V                      |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{mb} \leq 120\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>       | -   | 16  | A                      |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 140 | A                      |
|              |                                      | full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$   | -   | 150 | A                      |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN   | -   | 98  | $\text{A}^2\text{s}$   |
| $di_T/dt$    | rate of rise of on-state current     | $I_T = 20\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$  | -   | 100 | $\text{A}/\mu\text{s}$ |
| $I_{GM}$     | peak gate current                    |  | -   | 2   | A                      |
| $P_{GM}$     | peak gate power                      |  | -   | 5   | W                      |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period  | -   | 0.5 | W                      |
| $T_{stg}$    | storage temperature                  |  | -40 | 150 | $^{\circ}\text{C}$     |
| $T_j$        | junction temperature                 |  | -   | 150 | $^{\circ}\text{C}$     |



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 120\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

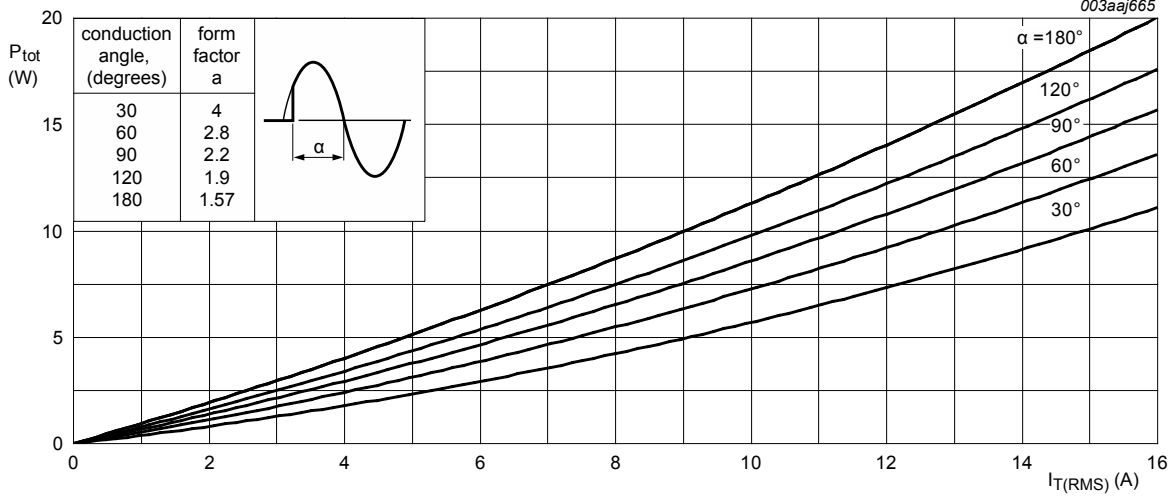


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

$\alpha =$  conduction angle

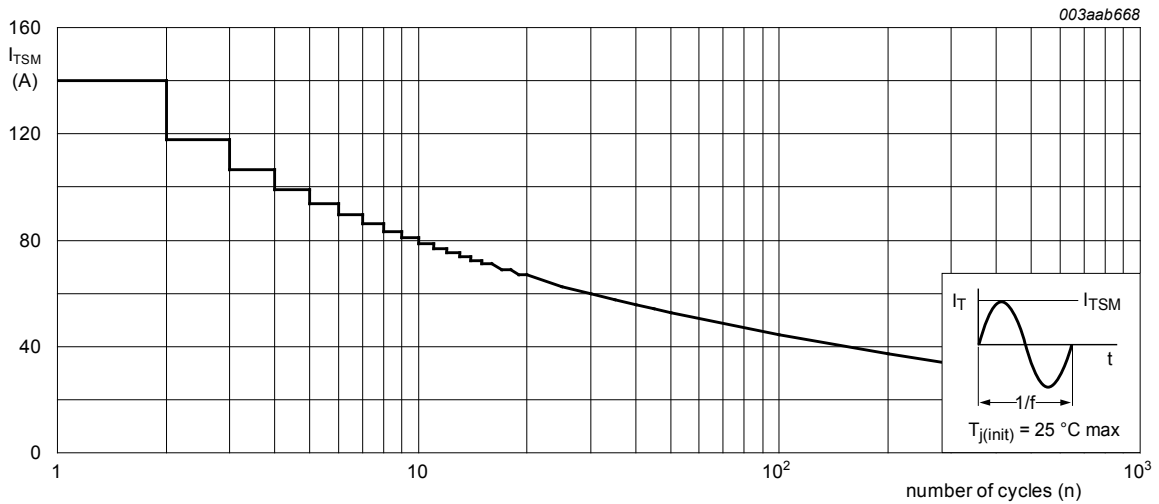


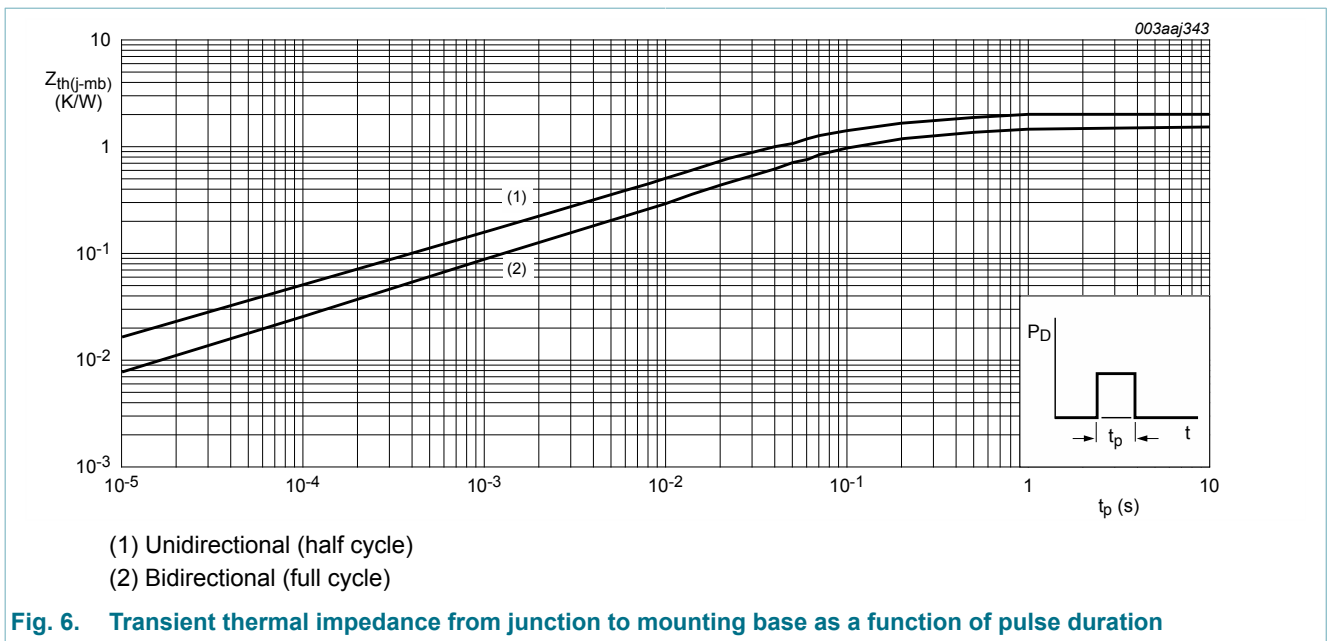
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 8. Thermal characteristics

Table 5. Thermal characteristics

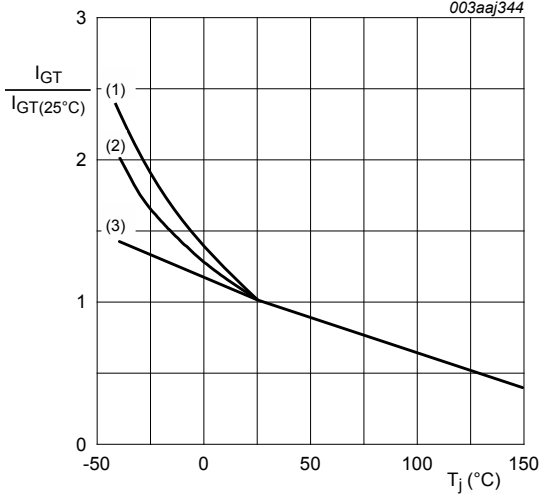
| Symbol         | Parameter   | Conditions                         | Min | Typ | Max | Unit |
|----------------|---|------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; <a href="#">Fig. 6</a> | -   | -   | 1.5 | K/W  |
|                |   | half cycle; <a href="#">Fig. 6</a> | -   | -   | 2   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air                        | -   | 60  | -   | K/W  |



## 9. Characteristics

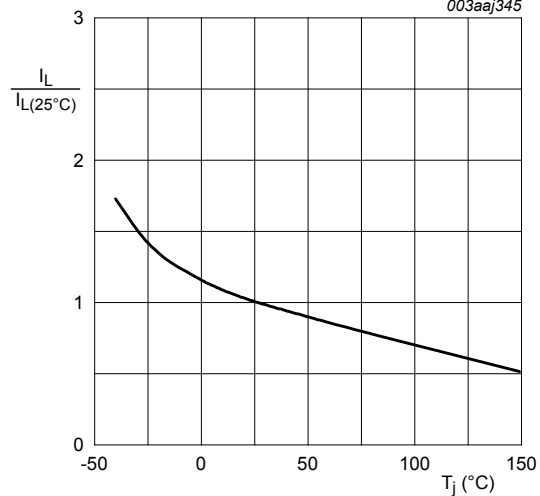
Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min  | Typ | Max | Unit       |
|--------------------------------|---------------------------------------|--|------|-----|-----|------------|
| <b>Static characteristics</b>  |                                       |  |      |     |     |            |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | 2    | -   | 50  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | 2    | -   | 50  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | 2    | -   | 50  | mA         |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -    | -   | 60  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -    | -   | 90  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>  | -    | -   | 60  | mA         |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -    | -   | 60  | mA         |
| $V_T$                          | on-state voltage                      | $I_T = 18\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -    | 1.3 | 1.5 | V          |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ;<br><a href="#">Fig. 11</a>   | -    | 0.8 | 1   | V          |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 150\text{ °C}$ ;<br><a href="#">Fig. 11</a>   | 0.25 | 0.4 | -   | V          |
| $I_D$                          | off-state current                     | $V_D = 600\text{ V}$ ; $T_j = 150\text{ °C}$   | -    | 0.1 | 0.5 | mA         |
| <b>Dynamic characteristics</b> |                                       |  |      |     |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit                                      | 1000 | -   | -   | V/ $\mu$ s |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 16\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit | 20   | -   | -   | A/ms       |

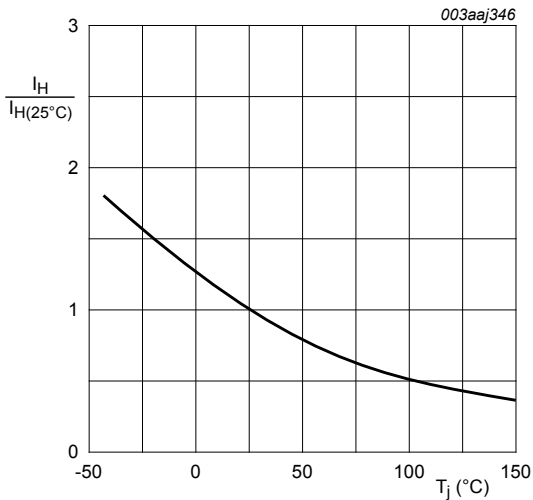


- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

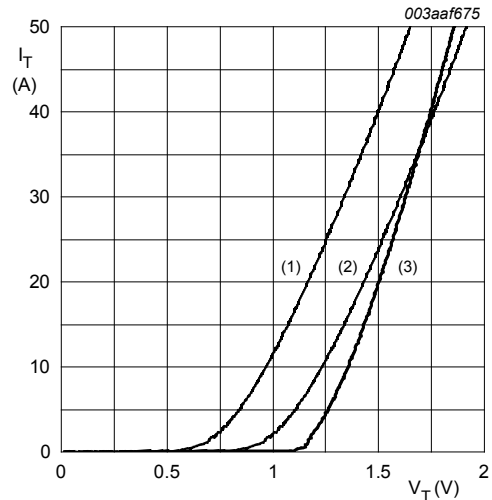
**Fig. 7. Normalized gate trigger current as a function of junction temperature**



**Fig. 8. Normalized latching current as a function of junction temperature**



**Fig. 9. Normalized holding current as a function of junction temperature**



$V_o = 1.024 \text{ V}$ ;  $R_s = 0.021 \Omega$

- (1)  $T_j = 150^\circ\text{C}$ ; typical values
- (2)  $T_j = 150^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**



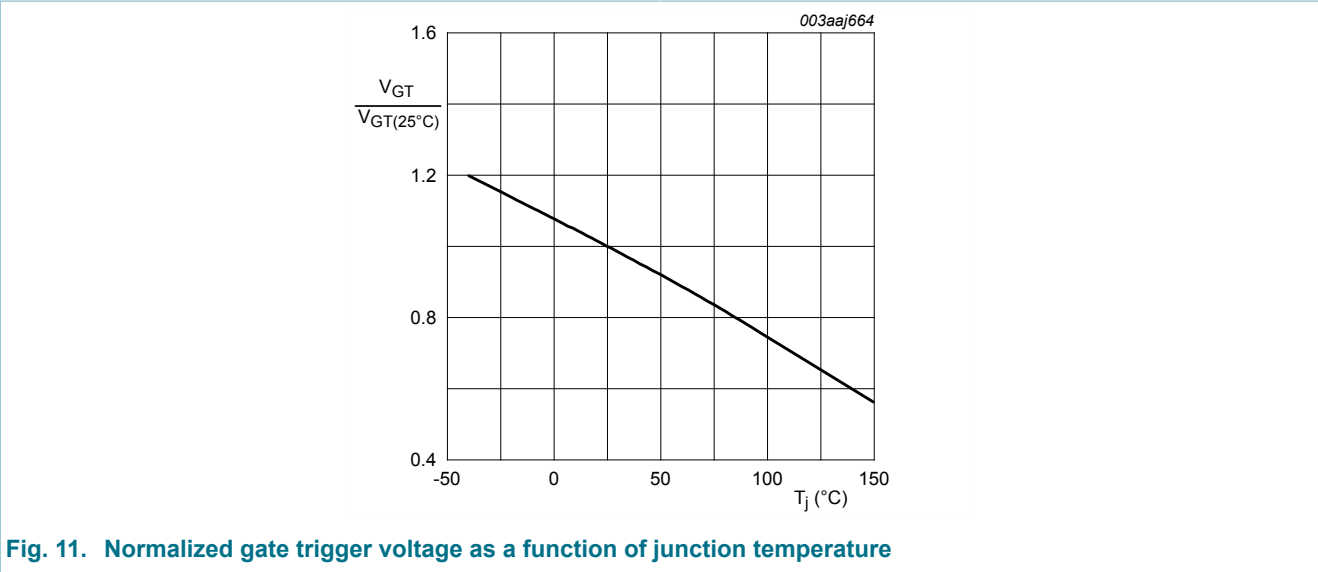


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

### 10. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) SOT404



Dimensions (mm are the original dimensions)

| Unit | A   | A <sub>1</sub> | b    | b <sub>2</sub> | c    | D  | D <sub>1</sub> | E    | e    | H <sub>D</sub> | L <sub>p</sub> | Q   |
|------|-----|----------------|------|----------------|------|----|----------------|------|------|----------------|----------------|-----|
| max  | 4.5 | 1.40           | 0.85 | 1.45           | 0.64 | 11 | 1.6            | 10.3 |      | 15.8           | 2.9            | 2.6 |
| nom  |     |                |      |                |      |    |                |      | 2.54 |                |                |     |
| min  | 4.1 | 1.27           | 0.60 | 1.05           | 0.46 |    | 1.2            | 9.7  |      | 14.8           | 2.1            | 2.2 |

sot404\_po

| Outline version | References |       |       | European projection | Issue date             |
|-----------------|------------|-------|-------|---------------------|------------------------|
|                 | IEC        | JEDEC | JEITA |                     |                        |
| SOT404          |            |       |       |                     | -06-03-16-<br>13-02-25 |

Fig. 12. Package outline D2PAK (SOT404)

### 11. Soldering

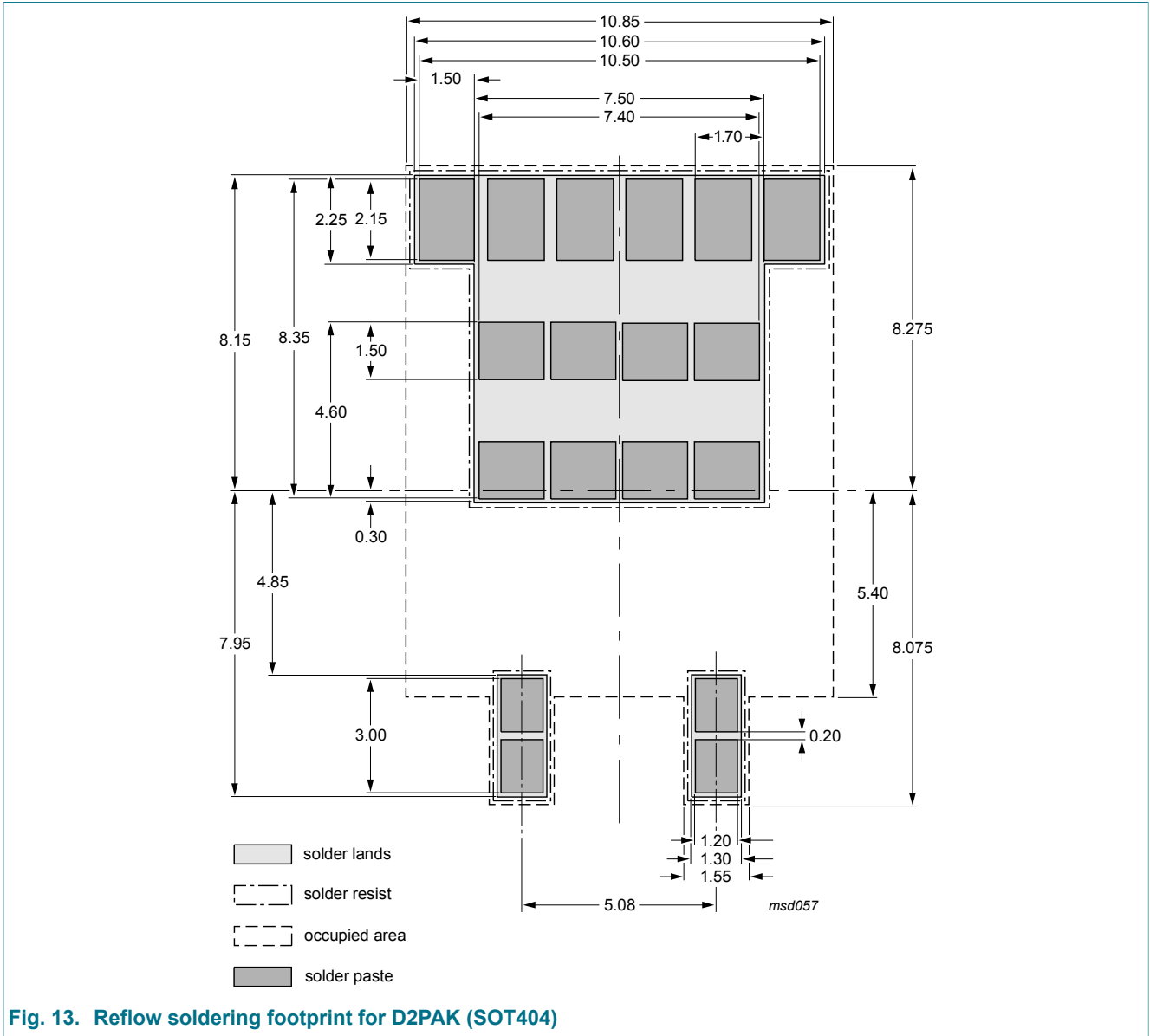


Fig. 13. Reflow soldering footprint for D2PAK (SOT404)

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| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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## 13. Contents

|      |                               |    |
|------|-------------------------------|----|
| 1    | General description .....     | 1  |
| 2    | Features and benefits .....   | 1  |
| 3    | Applications .....            | 1  |
| 4    | Quick reference data .....    | 1  |
| 5    | Pinning information .....     | 2  |
| 6    | Ordering information .....    | 2  |
| 7    | Limiting values .....         | 3  |
| 8    | Thermal characteristics ..... | 6  |
| 9    | Characteristics .....         | 7  |
| 10   | Package outline .....         | 10 |
| 11   | Soldering .....               | 11 |
| 12   | Legal information .....       | 12 |
| 12.1 | Data sheet status .....       | 12 |
| 12.2 | Definitions .....             | 12 |
| 12.3 | Disclaimers .....             | 12 |
| 12.4 | Trademarks .....              | 13 |

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